

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	("6610613").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/01 09:49
L2	7526	(silicon near nitride) near8 thickness near8 nm	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:04
L3	1016	(xenon near8 wavelength) near8 nm	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:01
L4	17	2 and 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:01
L5	15	4 and ((@ad<"20030623") or (@rlad<"20030623"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:06
L6	1691	2 and "NH.sub.3"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:04
L7	46	6 and (pressure near8 mTorr) and ((flow near rate) near8 sccm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:05
L8	38	7 and ((@ad<"20030623") or (@rlad<"20030623"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:06

US-PAT-NO: 6470824

DOCUMENT-IDENTIFIER: US 6470824 B2

TITLE: Semiconductor manufacturing apparatus

----- KWIC -----

Brief Summary Text - BSTX (31):

For instance, Japanese Patent Laid-open Application (KOKAI) Nos.
HEI

5-36899 and HEI 9-50996 disclose an example of stacking a silicon
nitride film
due to thermal nitriding and silicon nitride film due to vapor phase
growth

method. In an example disclosed in HEI 5-36899, polycrystalline
silicon is

patterned in a prescribed shape to form an electrode, followed by
fast thermal

nitriding at 850.degree. C. for 60 sec with an annealing furnace to
form a

silicon nitride film of a film thickness of approximate several nm on
a surface

of the electrode due to thermal nitriding. On the surface of this
silicon

nitride film, a silicon nitride film of approximately 4 nm is
deposited due to

low-pressure vapor phase growth method.